

Dual N-Channel 25-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, e}	Q_g (Typ.)
25	0.0195 at $V_{GS} = 4.5$ V	8	11
	0.026 at $V_{GS} = 2.5$ V	8	

FEATURES

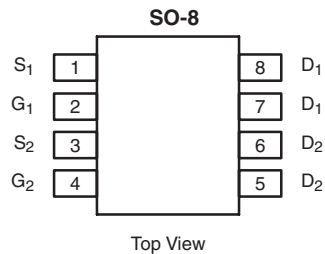
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

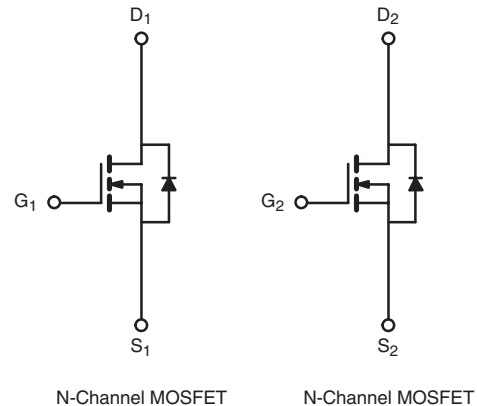
- Synchronous Buck Converter



RoHS
COMPLIANT



Ordering Information: Si4226DY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Pulsed Drain Current (10 μs Pulse Width)	I_{DM}	30	A
Source-Drain Current Diode Current	I_S	$T_C = 25^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
Pulsed Source-Drain Current	I_{SM}	30	
Single Pulse Avalanche Current	I_{AS}	10	mJ
Single Pulse Avalanche Energy	E_{AS}	5	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	50	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	R_{thJF}	30	38	

Notes:

- Based on $T_C = 25^\circ\text{C}$.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 110 $^\circ\text{C/W}$.
- Package limited.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	25			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		26		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 4			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6		2.0	V	
Gate Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 25 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 7 A		0.0155	0.0195	Ω	
		V _{GS} = 2.5 V, I _D = 5 A		0.020	0.026		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7 A		40		S	
Dynamic ^a							
Input Capacitance	C _{iss}	N-Channel V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1255		pF	
Output Capacitance	C _{oss}			185			
Reverse Transfer Capacitance	C _{rss}			90			
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 8 A		24	36	nC	
Gate-Source Charge	Q _{gs}	N-Channel V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 8 A		11	17		
Gate-Drain Charge	Q _{gd}			2			
Gate Resistance	R _g			2.5			
Turn-On Delay Time	t _{d(on)}	f = 1 MHz	0.3	1.4	2.8	Ω	
Rise Time	t _r		N-Channel V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		8		16
Turn-Off Delay Time	t _{d(off)}				9		18
Fall Time	t _f				24		40
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω			8	16	
Rise Time	t _r			14	25		
Turn-Off Delay Time	t _{d(off)}			10	20		
Fall Time	t _f			30	50		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			2.6	A	
Pulse Diode Forward Current ^a	I _{SM}				30		
Body Diode Voltage	V _{SD}	I _S = 2 A		0.73	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		25	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			14	28	nC	
Reverse Recovery Fall Time	t _a			12		ns	
Reverse Recovery Rise Time	t _b			13			

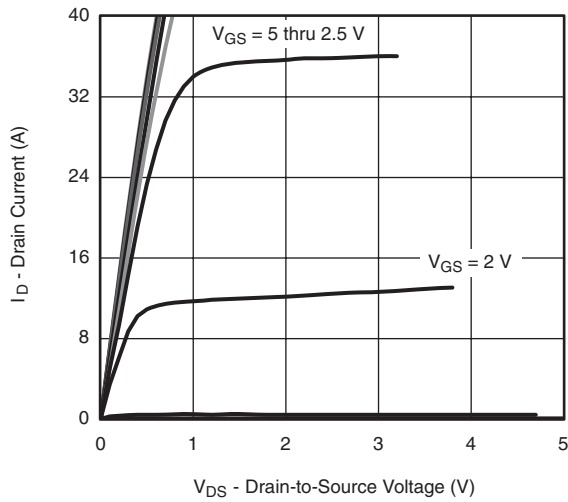
Notes:

a. Guaranteed by design, not subject to production testing.

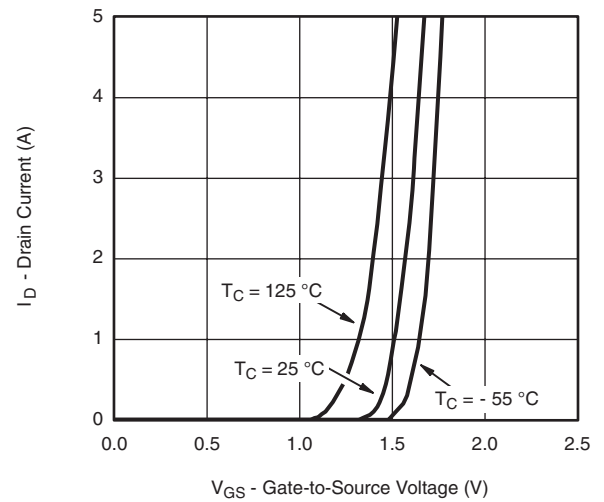
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

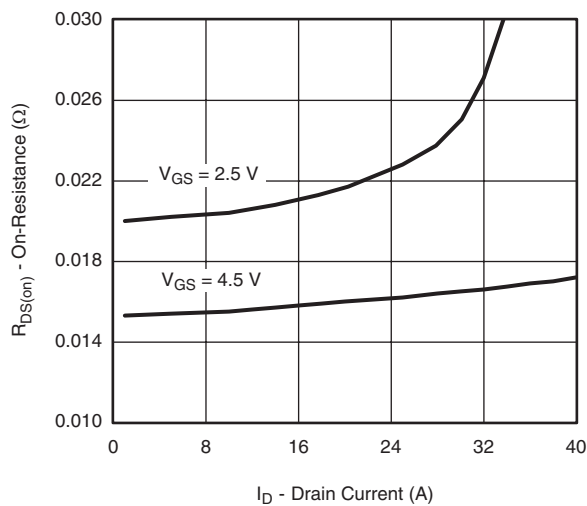
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



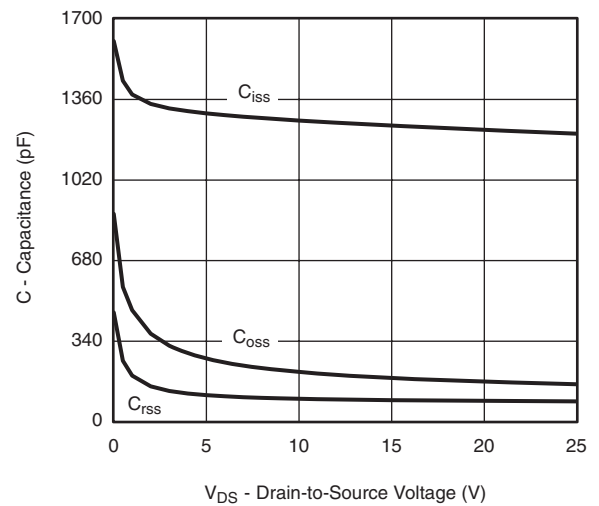
Output Characteristics



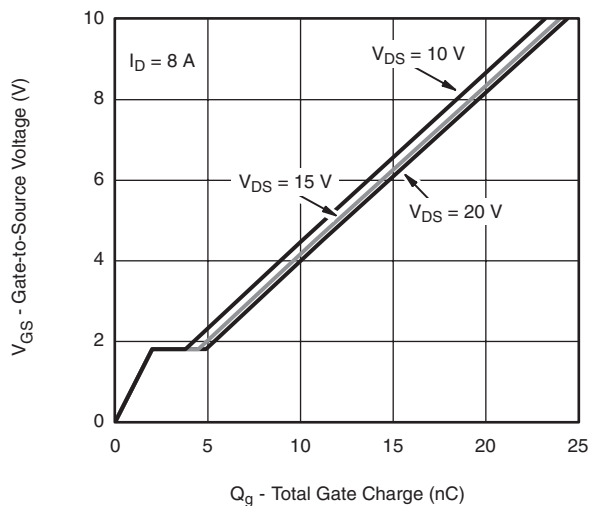
Transfer Characteristics



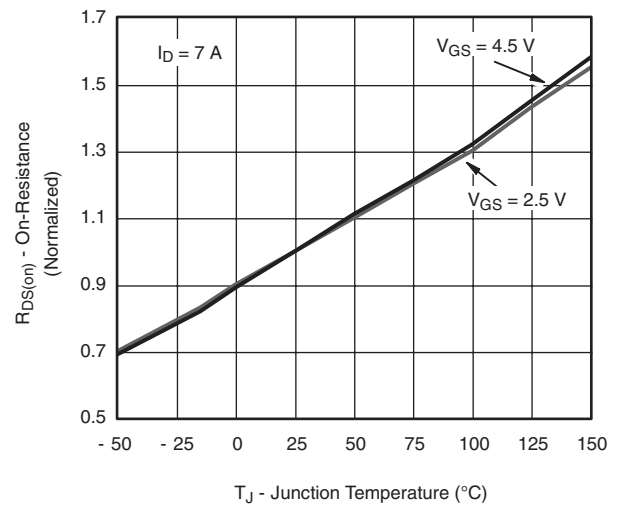
On-Resistance vs. Drain Current



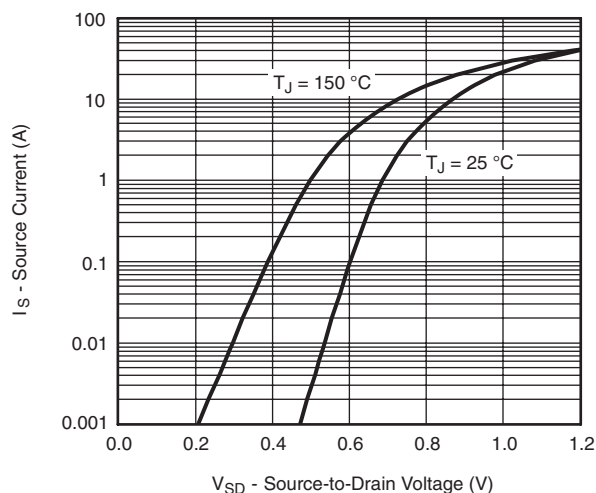
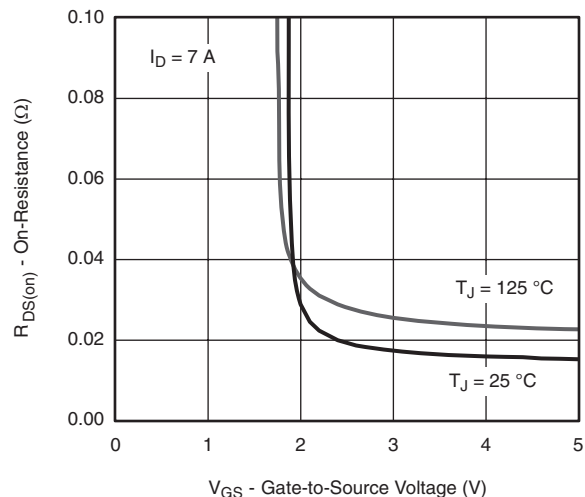
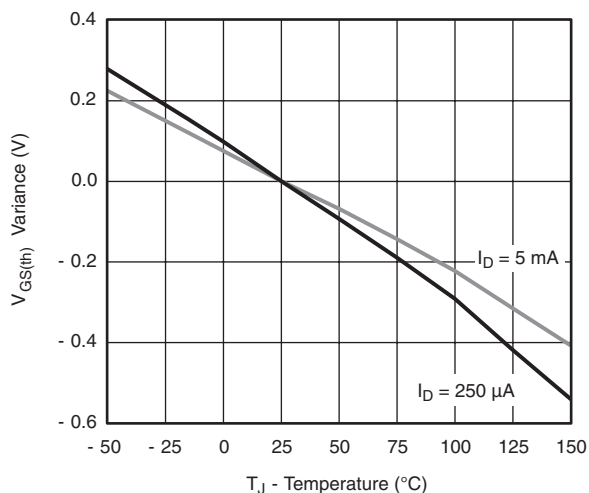
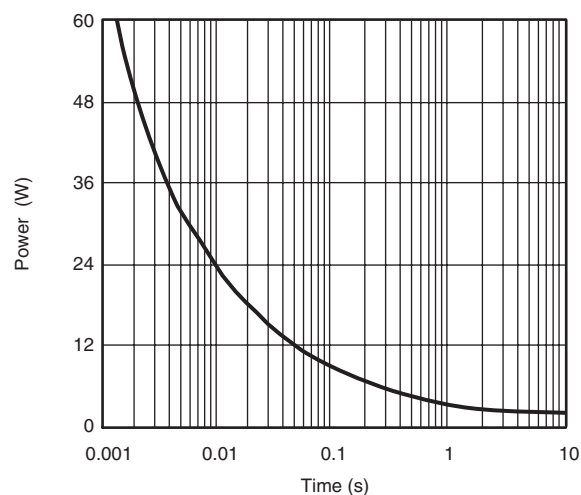
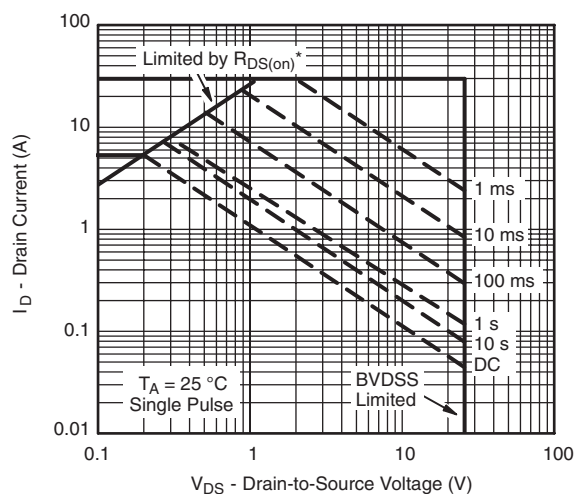
Capacitance



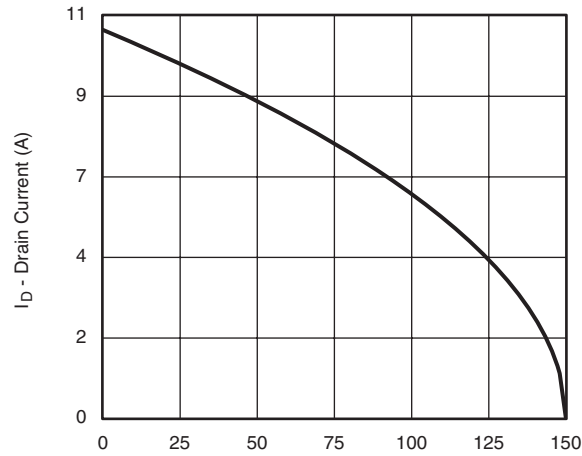
Gate Charge



On-Resistance vs. Junction Temperature

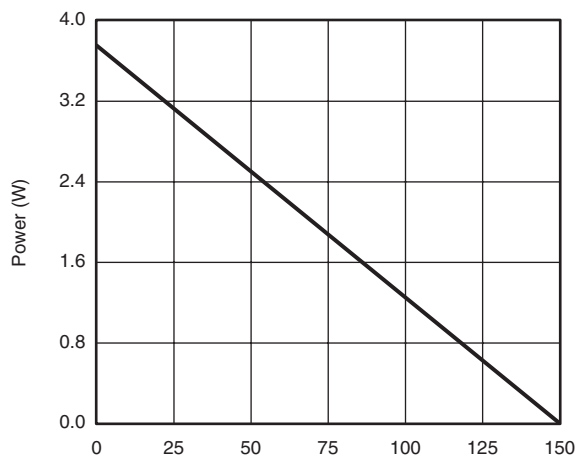
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**

MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



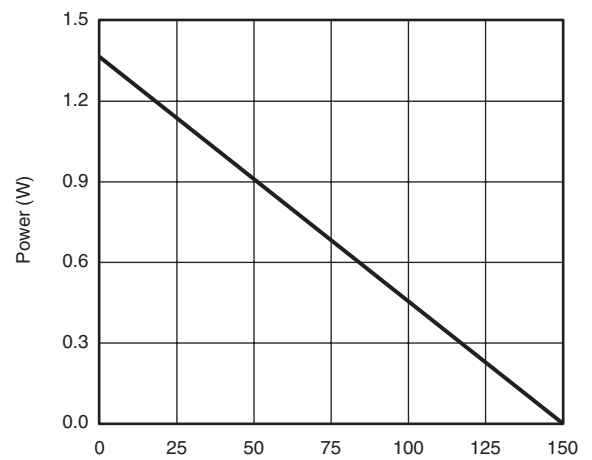
T_C - Case Temperature (°C)

Current Derating*



T_C - Case Temperature (°C)

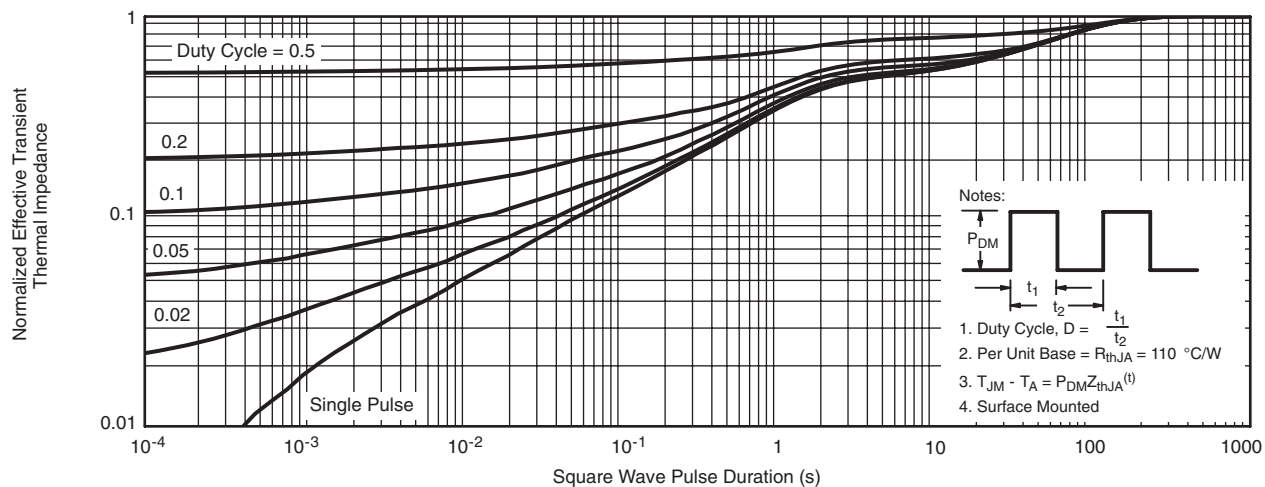
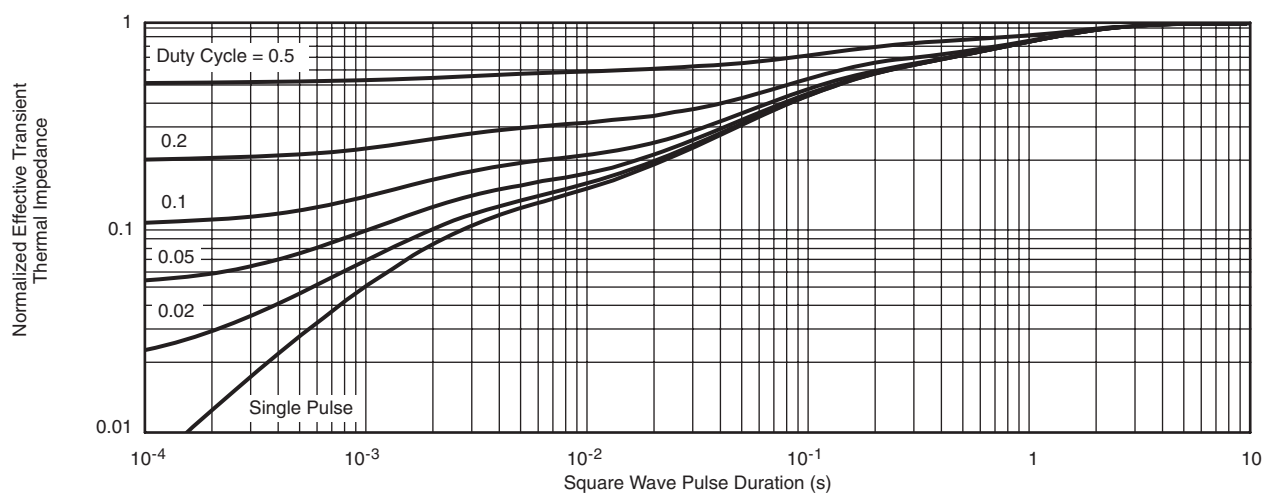
Power, Junction-to-Foot



T_C - Case Temperature (°C)

Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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